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Understanding Embedded - Microprocessors

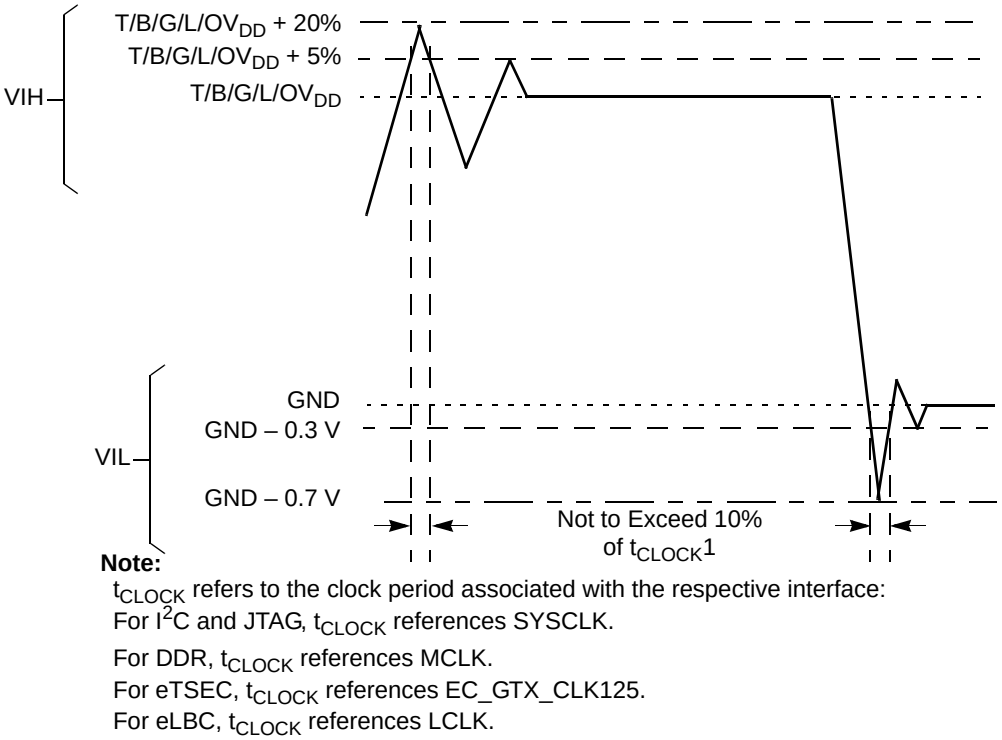
Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	2 Core, 32-Bit
Speed	1.5GHz
Co-Processors/DSP	Signal Processing; SPE, Security; SEC
RAM Controllers	DDR2, DDR3
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.5V, 1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	1023-BBGA, FCBGA
Supplier Device Package	1023-FCPBGA (33x33)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8572evjavne

Figure 2 shows the undershoot and overshoot voltages at the interfaces of the MPC8572E.



Note:
t_{CLOCK} refers to the clock period associated with the respective interface:
For I^2C and JTAG, t_{CLOCK} references SYSCLK.
For DDR, t_{CLOCK} references MCLK.
For eTSEC, t_{CLOCK} references EC_GTX_CLK125.
For eLBC, t_{CLOCK} references LCLK.

Figure 2. Overshoot/Undershoot Voltage for $TV_{DD}/BV_{DD}/GV_{DD}/LV_{DD}/OV_{DD}$

The core voltage must always be provided at nominal 1.1 V. (See Table 2 for actual recommended core voltage.) Voltage to the processor interface I/Os are provided through separate sets of supply pins and must be provided at the voltages shown in Table 2. The input voltage threshold scales with respect to the associated I/O supply voltage. TV_{DD}, BV_{DD}, OV_{DD}, and LV_{DD} based receivers are simple CMOS I/O circuits and satisfy appropriate LVCMOS type specifications. The DDR2 and DDR3 SDRAM interface uses differential receivers referenced by the externally supplied $MV_{REF}n$ signal (nominally set to $GV_{DD}/2$) as is appropriate for the SSTL_1.8 electrical signaling standard for DDR2 or 1.5-V electrical signaling for DDR3. The DDR DQS receivers cannot be operated in single-ended fashion. The complement signal must be properly driven and cannot be grounded.

Table 11. DDR2 SDRAM Interface DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V (continued)

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. $MV_{REF}n$ is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on $MV_{REF}n$ may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to that far end signal termination is made and is expected to be equal to $MV_{REF}n$. This rail should track variations in the DC level of $MV_{REF}n$.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

Table 12 provides the recommended operating conditions for the DDR SDRAM controller of the MPC8572E when interfacing to DDR3 SDRAM.

Table 12. DDR3 SDRAM Interface DC Electrical Characteristics for GV_{DD}(typ) = 1.5 V

Parameter/Condition	Symbol	Min	Typical	Max	Unit
I/O supply voltage	GV_{DD}	1.425	1.575	V	1
I/O reference voltage	$MV_{REF}n$	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
Input high voltage	V_{IH}	$MV_{REF}n$ + 0.100	GV_{DD}	V	—
Input low voltage	V_{IL}	GND	$MV_{REF}n$ – 0.100	V	—
Output leakage current	I_{OZ}	–50	50	µA	3

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. $MV_{REF}n$ is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on $MV_{REF}n$ may not exceed ±1% of the DC value.
3. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

Table 13 provides the DDR SDRAM controller interface capacitance for DDR2 and DDR3.

Table 13. DDR2 and DDR3 SDRAM Interface Capacitance for GV_{DD}(typ)=1.8 V and 1.5 V

Parameter/Condition	Symbol	Min	Typical	Max	Unit
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1, 2
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1, 2

Note:
1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V (for DDR2), f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.
2. This parameter is sampled. GV_{DD} = 1.5 V ± 0.075 V (for DDR3), f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.175 V.

The Fast Ethernet Controller (FEC) operates in MII mode only, and complies with the AC and DC electrical characteristics specified in this chapter for MII. Note that if FEC is used, eTSEC 3 and 4 are only available in SGMII mode.

8.1.1 eTSEC DC Electrical Characteristics

All MII, GMII, RMII, and TBI drivers and receivers comply with the DC parametric attributes specified in Table 23 and Table 24. All RGMII, RTBI and FIFO drivers and receivers comply with the DC parametric attributes specified in Table 24. The RGMII and RTBI signals are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Table 23. GMII, MII, RMII, and TBI DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
Supply voltage 3.3 V	LV_{DD} TV_{DD}	3.13	3.47	V	1, 2
Output high voltage (LV_{DD}/TV_{DD} = Min, IOH = –4.0 mA)	VOH	2.40	LV_{DD}/TV_{DD} + 0.3	V	—
Output low voltage (LV_{DD}/TV_{DD} = Min, IOL = 4.0 mA)	VOL	GND	0.50	V	—
Input high voltage	V_{IH}	2.0	LV_{DD}/TV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	0.90	V	—
Input high current (V_{IN} = LV_{DD}, V_{IN} = TV_{DD})	I_{IH}	—	40	µA	1, 2,3
Input low current (V_{IN} = GND)	I_{IL}	–600	—	µA	3

Notes:

1 LV_{DD} supports eTSECs 1 and 2.
2 TV_{DD} supports eTSECs 3 and 4 or FEC.
3 The symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1.

Table 24. MII, GMII, RMII, RGMII, TBI, RTBI, and FIFO DC Electrical Characteristics

Parameters	Symbol	Min	Max	Unit	Notes
Supply voltage 2.5 V	LV_{DD}/TV_{DD}	2.37	2.63	V	1,2
Output high voltage (LV_{DD}/TV_{DD} = Min, IOH = –1.0 mA)	V_{OH}	2.00	LV_{DD}/TV_{DD} + 0.3	V	—
Output low voltage (LV_{DD}/TV_{DD} = Min, I_{OL} = 1.0 mA)	V_{OL}	GND – 0.3	0.40	V	—
Input high voltage	V_{IH}	1.70	LV_{DD}/TV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	0.70	V	—

Figure 9 shows the GMII transmit AC timing diagram.

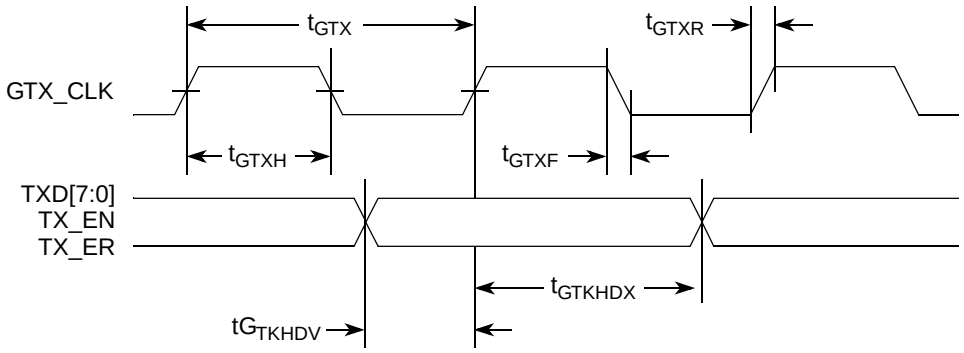


Figure 9. GMII Transmit AC Timing Diagram

8.2.2.2 GMII Receive AC Timing Specifications

Table 28 provides the GMII receive AC timing specifications.

Table 28. GMII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/TV_{DD} of 2.5/ 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
RX_CLK clock period	t_{GRX}	—	8.0	—	ns
RX_CLK duty cycle	t_{GRXH}/t_{GRX}	40	—	60	ns
RXD[7:0], RX_DV, RX_ER setup time to RX_CLK	t_{GRDVKH}	2.0	—	—	ns
RXD[7:0], RX_DV, RX_ER hold time to RX_CLK	t_{GRDXKH}	0	—	—	ns
RX_CLK clock rise (20%-80%)	t_{GRXR}[2]	—	—	1.0	ns
RX_CLK clock fall time (80%-20%)	t_{GRXF}[2]	—	—	1.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Guaranteed by design.

Figure 10 provides the AC test load for eTSEC.

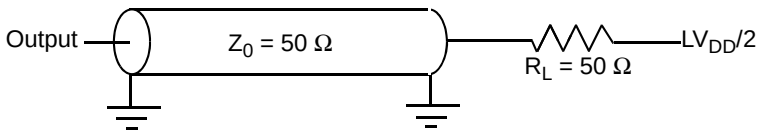


Figure 10. eTSEC AC Test Load

Figure 15 shows the TBI transmit AC timing diagram.

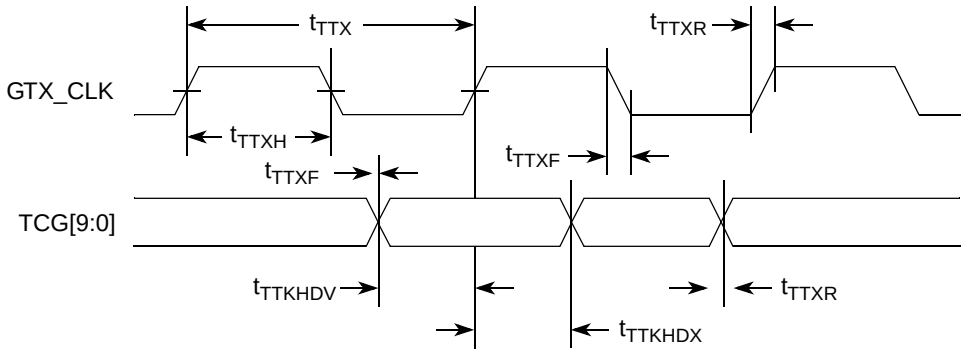


Figure 15. TBI Transmit AC Timing Diagram

8.2.4.2 TBI Receive AC Timing Specifications

Table 32 provides the TBI receive AC timing specifications.

Table 32. TBI Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/TV_{DD} of 2.5/ 3.3 V ± 5%.

Parameter/Condition [3]	Symbol [1]	Min	Typ	Max	Unit
Clock period for TBI Receive Clock 0, 1	t_{TRX}	—	16.0	—	ns
Skew for TBI Receive Clock 0, 1	t_{SKTRX}	7.5	—	8.5	ns
Duty cycle for TBI Receive Clock 0, 1	t_{TRXH}/t_{TRX}	40	—	60	%
RCG[9:0] setup time to rising edge of TBI Receive Clock 0, 1	t_{TRDVKH}	2.5	—	—	ns
RCG[9:0] hold time to rising edge of TBI Receive Clock 0, 1	t_{TRDXKH}	1.5	—	—	ns
Clock rise time (20%-80%) for TBI Receive Clock 0, 1	t_{TRXR} [2]	0.7	—	2.4	ns
Clock fall time (80%-20%) for TBI Receive Clock 0, 1	t_{TRXF} [2]	0.7	—	2.4	ns

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{TRDVKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{TRX} clock reference (K) going to the high (H) state or setup time. Also, t_{TRDXKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) went invalid (X) relative to the t_{TRX} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{TRX} represents the TBI (T) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall). For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (TRX).
2. Guaranteed by design.
3. The signals “TBI Receive Clock 0” and “TBI Receive Clock 1” refer to TSECn_RX_CLK and TSECn_TX_CLK pins respectively. These two clock signals are also referred as PMA_RX_CLK[0:1].

Figure 17 shows the TBI receive the timing diagram.

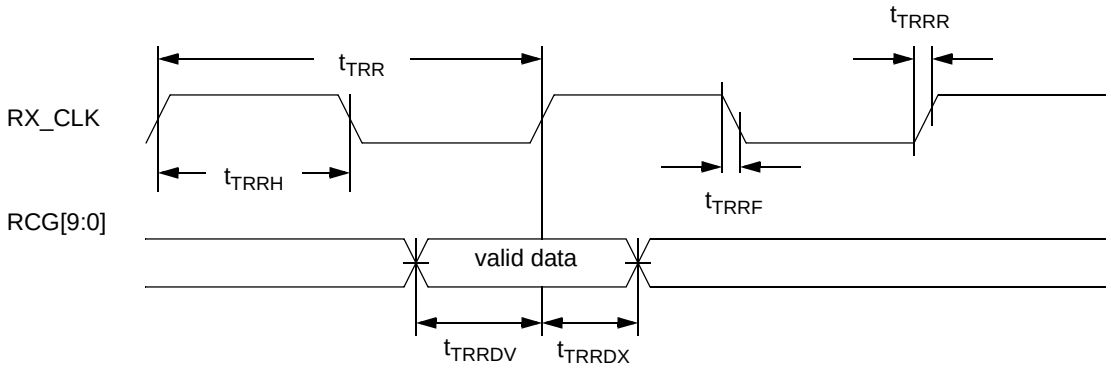


Figure 17. TBI Single-Clock Mode Receive AC Timing Diagram

8.2.6 RGMII and RTBI AC Timing Specifications

Table 34 presents the RGMII and RTBI AC timing specifications.

Table 34. RGMII and RTBI AC Timing Specifications

At recommended operating conditions with LV_{DD}/TV_{DD} of 2.5 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
Data to clock output skew (at transmitter)	t_{SKRGT}	–500	0	500	ps
Data to clock input skew (at receiver) [2]	t_{SKRGT}	1.0	—	2.8	ns
Clock period [3]	t_{RGT}	7.2	8.0	8.8	ns
Duty cycle for 10BASE-T and 100BASE-TX [3, 4]	t_{RGTH}/t_{RGT}	40	50	60	%
Rise time (20%–80%)	t_{RGTR}	—	—	0.75	ns
Fall time (20%–80%)	t_{RGTF}	—	—	0.75	ns

Notes:

1. Note that, in general, the clock reference symbol representation for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Note also that the notation for rise (R) and fall (F) times follows the clock symbol that is being represented. For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (RGT).
2. This implies that PC board design requires clocks to be routed such that an additional trace delay of greater than 1.5 ns will be added to the associated clock signal.
3. For 10 and 100 Mbps, t_{RGT} scales to 400 ns ± 40 ns and 40 ns ± 4 ns, respectively.
4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet's clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned between.

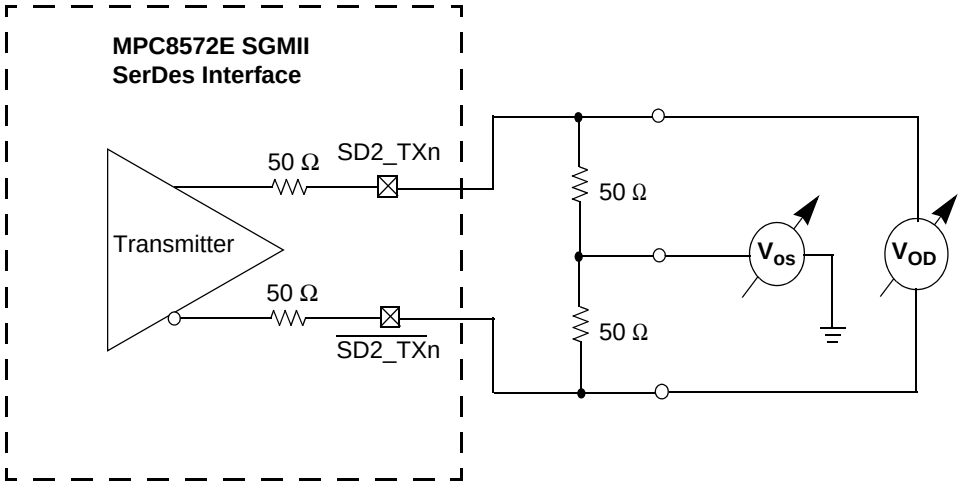


Figure 23. SGMII Transmitter DC Measurement Circuit

Table 39 lists the SGMII DC receiver electrical characteristics.

Table 39. SGMII DC Receiver Electrical Characteristics

Parameter		Symbol	Min	Typ	Max	Unit	Notes
Supply Voltage		XV_{DD_SRDS2}	1.045	1.1	1.155	V	—
DC Input voltage range		—	N/A			—	1
Input differential voltage	LSTS = 0	$V_{RX\_DIFFp-p}$	100	—	1200	mV	2, 4
	LSTS = 1		175	—			
Loss of signal threshold	LSTS = 0	VLOS	30	—	100	mV	3, 4
	LSTS = 1		65	—	175		
Input AC common mode voltage		V_{CM_ACp-p}		—	100	mV	5
Receiver differential input impedance		Z_{RX_DIFF}	80	100	120	Ω	—
Receiver common mode input impedance		Z_{RX_CM}	20	—	35	Ω	—
Common mode input voltage		V_{CM}	—	$V_{xcorevss}$	—	V	6

Note:

1. Input must be externally AC-coupled.
2. $V_{RX\_DIFFp-p}$ is also referred to as peak to peak input differential voltage
3. The concept of this parameter is equivalent to the Electrical Idle Detect Threshold parameter in PCI Express. Refer to PCI Express Differential Receiver (RX) Input Specifications section for further explanation.
4. The LSTS shown in the table refers to the LSTS**AB** or LSTS**EF** bit field of MPC8572E's SerDes 2 Control Register.
5. V_{CM_ACp-p} is also referred to as peak to peak AC common mode voltage.
6. On-chip termination to SGND_SRDS2 (xcorevss).

Table 49. Local Bus General Timing Parameters (BV_{DD} = 3.3 V DC)—PLL Enabled (continued)

At recommended operating conditions with BV_{DD} of 3.3 V ± 5%. (continued)

Parameter	Symbol [1]	Min	Max	Unit	Notes
Local bus clock to LALE assertion	$t_{LBKHOV4}$	—	2.3	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	0.7	—	ns	3
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	0.7	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKHOZ1}$	—	2.5	ns	5
Local bus clock to output high impedance for LAD/LDP	$t_{LBKHOZ2}$	—	2.5	ns	5

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
3. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is programmed with the LBCR[AHD] parameter.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $BV_{DD}/2$.
8. Guaranteed by design.

Table 50 describes the general timing parameters of the local bus interface at BV_{DD} = 2.5 V DC.

Table 50. Local Bus General Timing Parameters (BV_{DD} = 2.5 V DC)—PLL Enabled

At recommended operating conditions with BV_{DD} of 2.5 V ± 5%

Parameter	Symbol [1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	6.67	12	ns	2
Local bus duty cycle	t_{LBKH}/t_{LBK}	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	$t_{LBKSKEW}$	—	150	ps	7, 8
Input setup to local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIVKH1}$	1.9	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	1.8	—	ns	3, 4
Input hold from local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIXKH1}$	1.1	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input hold from local bus clock	$t_{LBIXKH2}$	1.1	—	ns	3, 4
LALE output negation to high impedance for LAD/LDP (LATCH hold time)	t_{LBOTOT}	1.5	—	ns	6

Figure 30 through Figure 35 show the local bus signals.

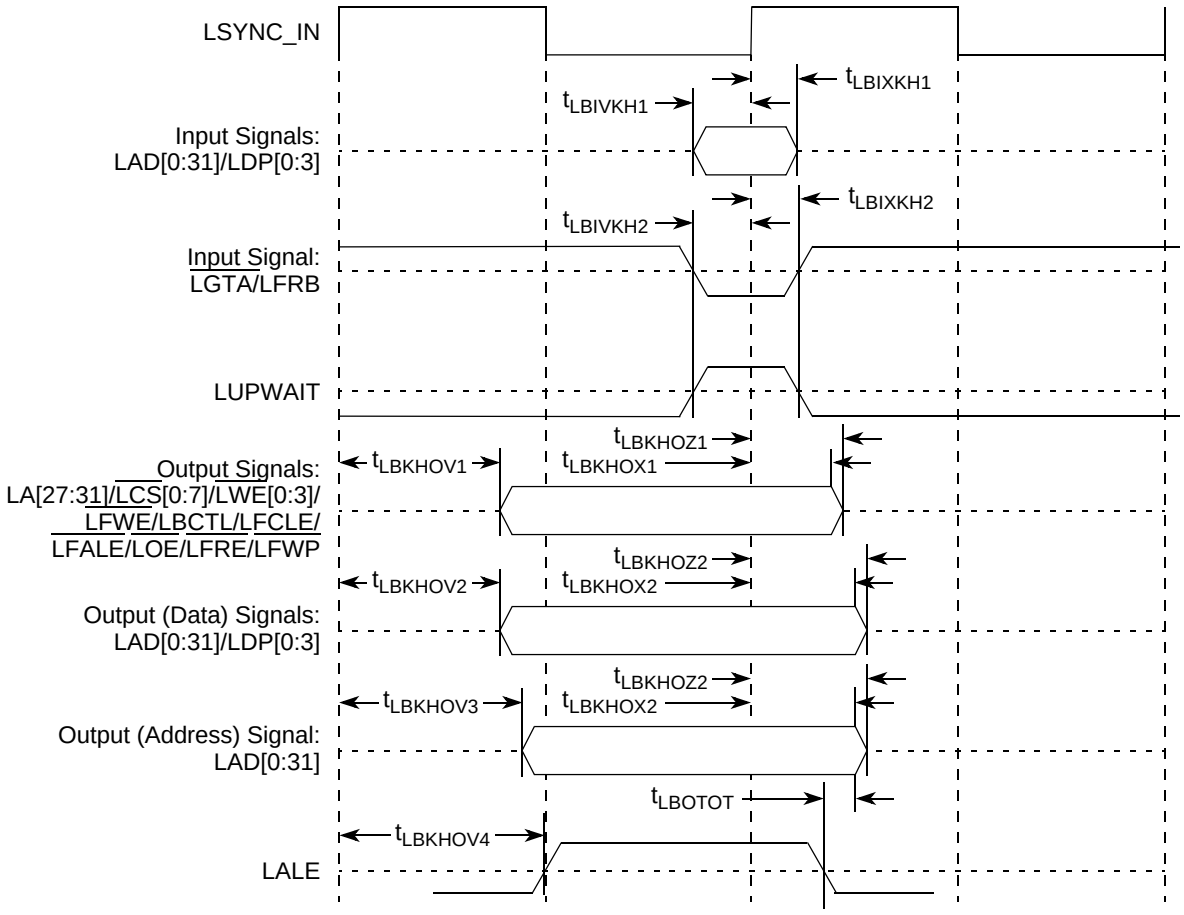


Figure 30. Local Bus Signals, Non-Special Signals Only (PLL Enabled)

Table 52 describes the general timing parameters of the local bus interface at BV_{DD} = 3.3 V DC with PLL disabled.

Table 52. Local Bus General Timing Parameters—PLL Bypassed

At recommended operating conditions with BV_{DD} of 3.3 V ± 5%

Parameter	Symbol [1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	12	—	ns	2
Local bus duty cycle	t_{LBKH}/t_{LBK}	43	57	%	—
Internal launch/capture clock to LCLK delay	t_{LBKHKT}	2.3	4.0	ns	—
Input setup to local bus clock (except LGTA/LUPWAIT)	$t_{LBIVKH1}$	5.8	—	ns	4, 5
LGTA/LUPWAIT input setup to local bus clock	$t_{LBIVKL2}$	5.7	—	ns	4, 5
Input hold from local bus clock (except LGTA/LUPWAIT)	$t_{LBIXKH1}$	-1.3	—	ns	4, 5

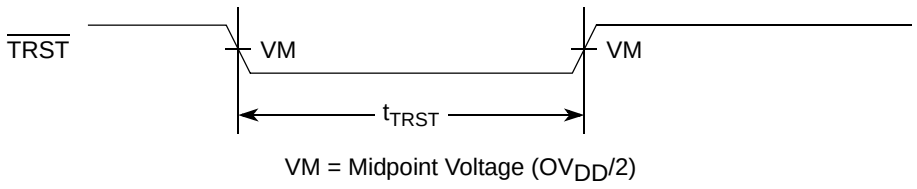


Figure 38. $\overline{\text{TRST}}$ Timing Diagram

Figure 39 provides the boundary-scan timing diagram.

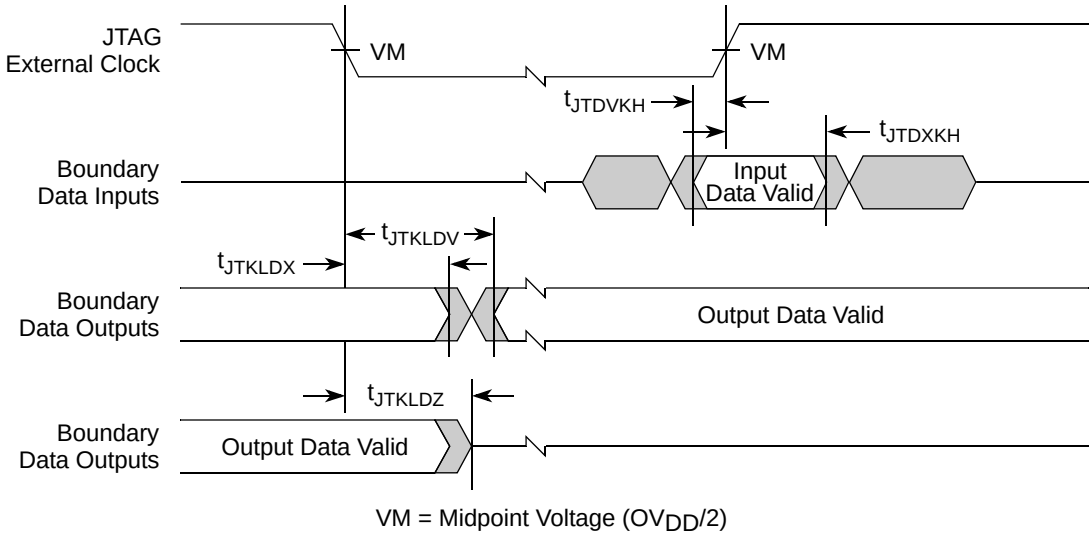


Figure 39. Boundary-Scan Timing Diagram

13 I²C

This section describes the DC and AC electrical characteristics for the I²C interfaces of the MPC8572E.

13.1 I²C DC Electrical Characteristics

Table 54 provides the DC electrical characteristics for the I²C interfaces.

Table 54. I²C DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	$OV_{DD} + 0.3$	V	—
Input low voltage level	V_{IL}	–0.3	$0.3 \times OV_{DD}$	V	—
Low level output voltage	V_{OL}	0	0.4	V	1
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	2
Input current each I/O pin (input voltage is between $0.1 \times OV_{DD}$ and $0.9 \times OV_{DD}$(max)	I_I	–10	10	µA	3

— To meet the input amplitude requirement, the reference clock inputs might need to be DC or AC-coupled externally. For the best noise performance, the reference of the clock could be DC or AC-coupled into the unused phase (SD*n*_REF_CLK) through the same source impedance as the clock input (SD*n*_REF_CLK) in use.

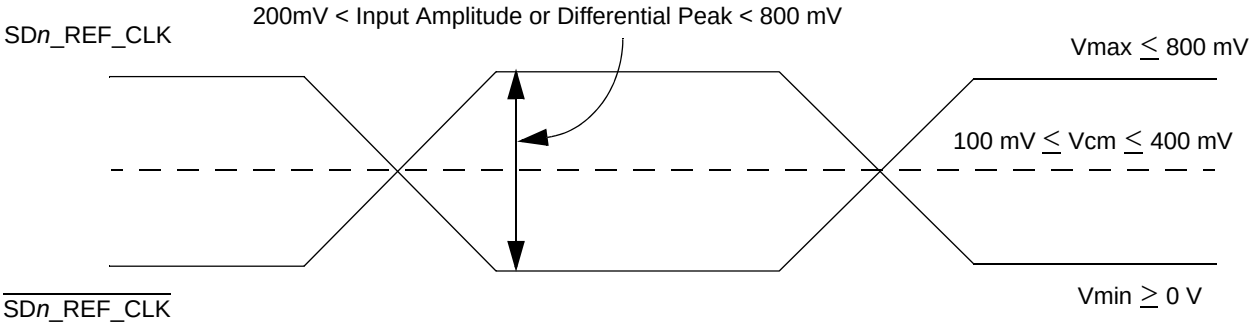


Figure 45. Differential Reference Clock Input DC Requirements (External DC-Coupled)

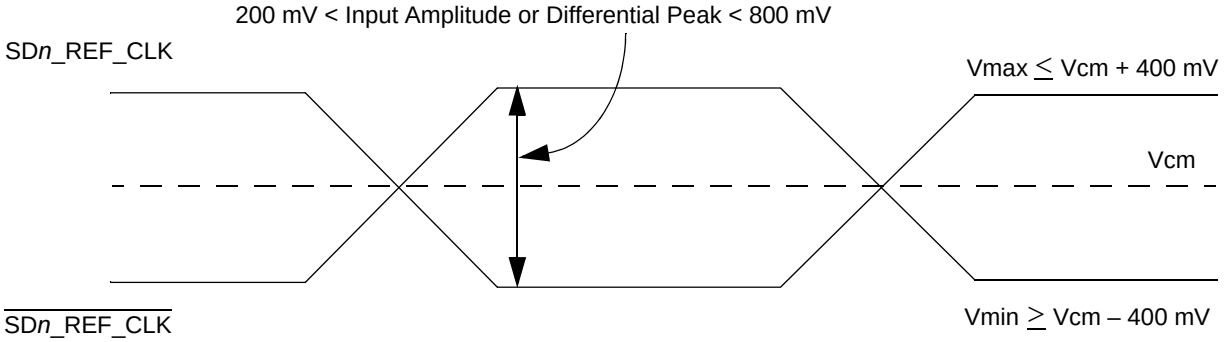


Figure 46. Differential Reference Clock Input DC Requirements (External AC-Coupled)

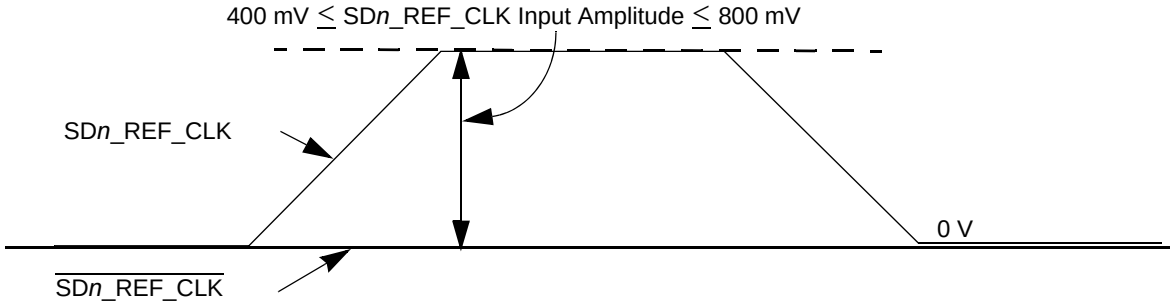


Figure 47. Single-Ended Reference Clock Input DC Requirements

Table 69. Long Run Transmitter AC Timing Specifications—2.5 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Output Voltage,	V_O	–0.40	2.30	Volts	Voltage relative to COMMON of either signal comprising a differential pair
Differential Output Voltage	V_{DIFFPP}	800	1600	mV p-p	—
Deterministic Jitter	J_D	—	0.17	UI p-p	—
Total Jitter	J_T	—	0.35	UI p-p	—
Multiple output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit Interval	UI	400	400	ps	+/- 100 ppm

Table 70. Long Run Transmitter AC Timing Specifications—3.125 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Output Voltage,	V_O	–0.40	2.30	Volts	Voltage relative to COMMON of either signal comprising a differential pair
Differential Output Voltage	V_{DIFFPP}	800	1600	mV p-p	—
Deterministic Jitter	J_D	—	0.17	UI p-p	—
Total Jitter	J_T	—	0.35	UI p-p	—
Multiple output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit Interval	UI	320	320	ps	+/- 100 ppm

For each baud rate at which an LP-Serial transmitter is specified to operate, the output eye pattern of the transmitter shall fall entirely within the unshaded portion of the transmitter output compliance mask shown in Figure 58 with the parameters specified in Figure 71 when measured at the output pins of the device and the device is driving a 100 Ω +/–5% differential resistive load. The output eye pattern of an LP-Serial transmitter that implements pre-emphasis (to equalize the link and reduce inter-symbol interference) need only comply with the Transmitter Output Compliance Mask when pre-emphasis is disabled or minimized.

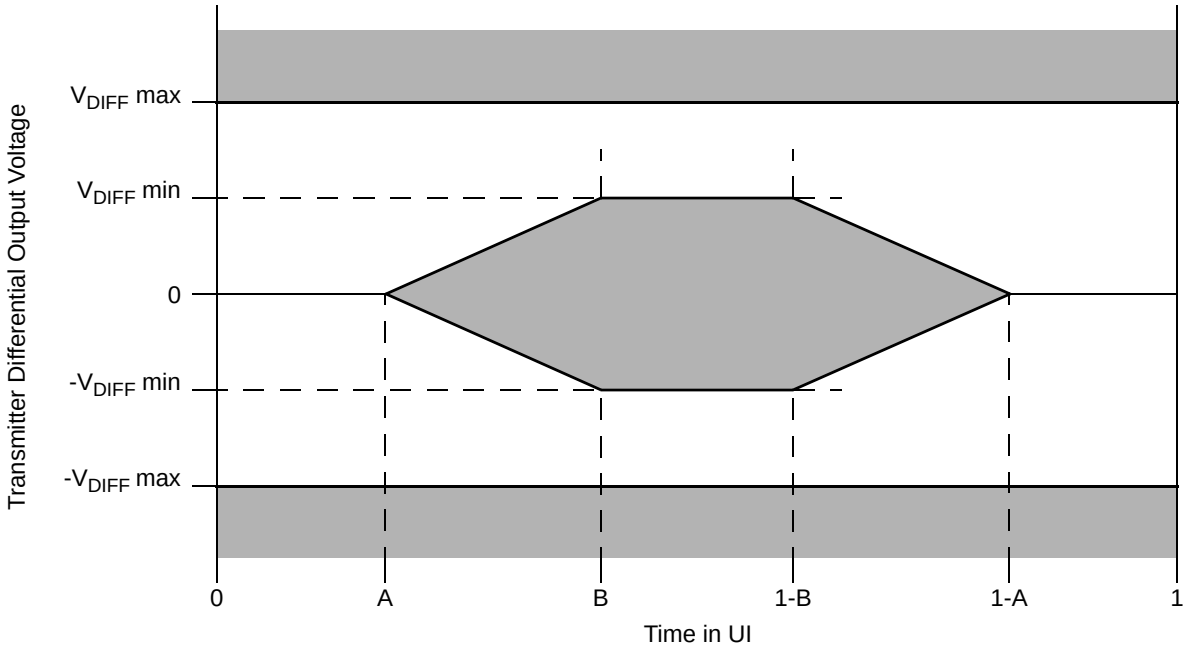


Figure 58. Transmitter Output Compliance Mask

Table 71. Transmitter Differential Output Eye Diagram Parameters

Transmitter Type	V_{DIFF}min (mV)	V_{DIFF}max (mV)	A (UI)	B (UI)
1.25 GBaud short range	250	500	0.175	0.39
1.25 GBaud long range	400	800	0.175	0.39
2.5 GBaud short range	250	500	0.175	0.39
2.5 GBaud long range	400	800	0.175	0.39
3.125 GBaud short range	250	500	0.175	0.39
3.125 GBaud long range	400	800	0.175	0.39

17.6 Receiver Specifications

LP-Serial receiver electrical and timing specifications are stated in the text and tables of this section.

Receiver input impedance shall result in a differential return loss better that 10 dB and a common mode return loss better than 6 dB from 100 MHz to (0.8) × (Baud Frequency). This includes contributions from on-chip circuitry, the chip package and any off-chip components related to the receiver. AC coupling components are included in this requirement. The reference impedance for return loss measurements is 100 Ohm resistive for differential return loss and 25-Ω resistive for common mode.

Table 76. MPC8572E Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{D1\_MCAS}}$	Column Address Strobe	AC9	O	GV_{DD}	—
$\overline{\text{D1\_MRAS}}$	Row Address Strobe	AB12	O	GV_{DD}	—
D1_MCKE[0:3]	Clock Enable	M8, L9, T9, N8	O	GV_{DD}	11
$\overline{\text{D1\_MCS}}$[0:3]	Chip Select	AB9, AF10, AB11, AE11	O	GV_{DD}	—
D1_MCK[0:5]	Clock	V7, E13, AH11, Y9, F14, AG10	O	GV_{DD}	—
$\overline{\text{D1\_MCK}}$[0:5]	Clock Complements	Y10, E12, AH12, AA11, F13, AG11	O	GV_{DD}	—
D1_MODT[0:3]	On Die Termination	AD10, AF12, AC10, AE12	O	GV_{DD}	—
D1_MDIC[0:1]	Driver Impedance Calibration	E15, G14	I/O	GV_{DD}	25
DDR SDRAM Memory Interface 2					
D2_MDQ[0:63]	Data	A6, B7, C5, D5, A7, C8, D8, D6, C4, A3, D3, D2, B4, A4, B1, C1, E3, E1, G2, G6, D1, E4, G5, G3, J4, J2, P4, R5, H3, H1, N5, N3, Y6, Y4, AC3, AD2, V5, W5, AB2, AB3, AD5, AE3, AF6, AG7, AC4, AD4, AF4, AF7, AH5, AJ1, AL2, AM3, AH3, AH6, AM1, AL3, AK5, AL5, AJ7, AK7, AK4, AM4, AL6, AM7	I/O	GV_{DD}	—
D2_MECC[0:7]	Error Correcting Code	J5, H7, L7, N6, H4, H6, M4, M5	I/O	GV_{DD}	—
$\overline{\text{D2\_MAPAR\_ERR}}$	Address Parity Error	N1	I	GV_{DD}	—
D2_MAPAR_OUT	Address Parity Out	W2	O	GV_{DD}	—
D2_MDM[0:8]	Data Mask	A5, B3, F4, J1, AA4, AE5, AK1, AM5, K5	O	GV_{DD}	—
D2_MDQS[0:8]	Data Strobe	B6, C2, F5, L4, AB5, AF3, AL1, AM6, L6	I/O	GV_{DD}	—
$\overline{\text{D2\_MDQS}}$[0:8]	Data Strobe	C7, A2, F2, K3, AA5, AE6, AK2, AJ6, K6	I/O	GV_{DD}	—
D2_MA[0:15]	Address	W1, U4, U3, T1, T2, T3, R1, R2, T5, R4, Y3, P1, N2, AF1, M2, M1	O	GV_{DD}	—

Table 76. MPC8572E Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
SD1_RX[7:0]	Receive Data (positive)	P32, N30, M32, L30, G30, F32, E30, D32	I	XV_{DD_SRDS1}	—
$\overline{\text{SD1\_RX}}$[7:0]	Receive Data (negative)	P31, N29, M31, L29, G29, F31, E29, D31	I	XV_{DD_SRDS1}	—
SD1_TX[7]	PCIe1 Tx Data Lane 7 / SRIO or PCIe2 Tx Data Lane 3 / PCIe3 TX Data Lane 1	M26	O	XV_{DD_SRDS1}	—
SD1_TX[6]	PCIe1 Tx Data Lane 6 / SRIO or PCIe2 Tx Data Lane 2 / PCIe3 TX Data Lane 0	L24	O	XV_{DD_SRDS1}	—
SD1_TX[5]	PCIe1 Tx Data Lane 5 / SRIO or PCIe2 Tx Data Lane 1	K26	O	XV_{DD_SRDS1}	—
SD1_TX[4]	PCIe1 Tx Data Lane 4 / SRIO or PCIe2 Tx Data Lane 0	J24	O	XV_{DD_SRDS1}	—
SD1_TX[3]	PCIe1 Tx Data Lane 3	G24	O	XV_{DD_SRDS1}	—
SD1_TX[2]	PCIe1 Tx Data Lane 2	F26	O	XV_{DD_SRDS1}	—
SD1_TX[1]	PCIe1 Tx Data Lane 1]	E24	O	XV_{DD_SRDS1}	—
SD1_TX[0]	PCIe1 Tx Data Lane 0	D26	O	XV_{DD_SRDS1}	—
$\overline{\text{SD1\_TX}}$[7:0]	Transmit Data (negative)	M27, L25, K27, J25, G25, F27, E25, D27	O	XV_{DD_SRDS1}	—
SD1_PLL_TPD	PLL Test Point Digital	J32	O	XV_{DD_SRDS1}	17
SD1_REF_CLK	PLL Reference Clock	H32	I	XV_{DD_SRDS1}	—
$\overline{\text{SD1\_REF\_CLK}}$	PLL Reference Clock Complement	H31	I	XV_{DD_SRDS1}	—
Reserved	—	C29, K32	—	—	26
Reserved	—	C30, K31	—	—	27
Reserved	—	C24, C25, H26, H27	—	—	28
Reserved	—	AL20, AL21	—	—	29
SerDes (x4) SGMII					
SD2_RX[3:0]	Receive Data (positive)	AK32, AJ30, AF30, AE32	I	XV_{DD_SRDS2}	—

Table 76. MPC8572E Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
MSRCID[0:1]	Memory Debug Source Port ID	U27, T29	O	OV_{DD}	5, 9, 30
MSRCID[2:4]	Memory Debug Source Port ID	U28, W24, W28	O	OV_{DD}	21
MDVAL	Memory Debug Data Valid	V26	O	OV_{DD}	2, 21
CLK_OUT	Clock Out	U32	O	OV_{DD}	11
Clock					
RTC	Real Time Clock	V25	I	OV_{DD}	—
SYSCLK	System Clock	Y32	I	OV_{DD}	—
DDRCLK	DDR Clock	AA29	I	OV_{DD}	31
JTAG					
TCK	Test Clock	T28	I	OV_{DD}	
TDI	Test Data In	T27	I	OV_{DD}	12
TDO	Test Data Out	T26	O	OV_{DD}	—
TMS	Test Mode Select	U26	I	OV_{DD}	12
$\overline{\text{TRST}}$	Test Reset	AA32	I	OV_{DD}	12
DFT					
L1_TSTCLK	L1 Test Clock	V32	I	OV_{DD}	18
L2_TSTCLK	L2 Test Clock	V31	I	OV_{DD}	18
$\overline{\text{LSSD\_MODE}}$	LSSD Mode	N24	I	OV_{DD}	18
$\overline{\text{TEST\_SEL}}$	Test Select 0	K28	I	OV_{DD}	18
Power Management					
ASLEEP	Asleep	P28	O	OV_{DD}	9, 15, 21

19 Clocking

This section describes the PLL configuration of the MPC8572E. Note that the platform clock is identical to the core complex bus (CCB) clock.

19.1 Clock Ranges

Table 77 provides the clocking specifications for both processor cores.

Table 77. MPC8572E Processor Core Clocking Specifications

Characteristic	Maximum Processor Core Frequency								Unit	Notes
	1067 MHz		1200 MHz		1333 MHz		1500 MHz			
	Min	Max	Min	Max	Min	Max	Min	Max		
e500 core processor frequency	800	1067	800	1200	800	1333	800	1500	MHz	1, 2
CCB frequency	400	533	400	533	400	533	400	600	MHz	
DDR Data Rate	400	667	400	667	400	667	400	800	MHz	

Notes:
1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. Refer to Section 19.2, “CCB/SYSCLK PLL Ratio,” Section 19.3, “e500 Core PLL Ratio,” and Section 19.4, “DDR/DDRCLK PLL Ratio,” for ratio settings.
2. The processor core frequency speed bins listed also reflect the maximum platform (CCB) and DDR data rate frequency supported by production test. Running CCB and/or DDR data rate higher than the limit shown above, although logically possible via valid clock ratio setting in some condition, is not supported.

The DDR memory controller can run in either synchronous or asynchronous mode. When running in synchronous mode, the memory bus is clocked relative to the platform clock frequency. When running in asynchronous mode, the memory bus is clocked with its own dedicated PLL with clock provided on DDRCLK input pin. Table 78 provides the clocking specifications for the memory bus.

Table 78. Memory Bus Clocking Specifications

Characteristic	Min	Max	Unit	Notes
Memory bus clock frequency	200	400	MHz	1, 2, 3, 4

Notes:
1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. Refer to Section 19.2, "CCB/SYSCLK PLL Ratio," Section 19.3, "e500 Core PLL Ratio," and Section 19.4, "DDR/DDRCLK PLL Ratio," for ratio settings.
2. The Memory bus clock refers to the MPC8572E memory controllers' Dn_MCK[0:5] and $\overline{\text{Dn\_MCK}}$[0:5] output clocks, running at half of the DDR data rate.
3. In synchronous mode, the memory bus clock speed is half the platform clock frequency. In other words, the DDR data rate is the same as the platform (CCB) frequency. If the desired DDR data rate is higher than the platform (CCB) frequency, asynchronous mode must be used.
4. In asynchronous mode, the memory bus clock speed is dictated by its own PLL. Refer to Section 19.4, "DDR/DDRCLK PLL Ratio." The memory bus clock speed must be less than or equal to the CCB clock rate which in turn must be less than the DDR data rate.

As a general guideline when selecting the DDR data rate or platform (CCB) frequency, the following procedures can be used:

- Start with the processor core frequency selection;
- After the processor core frequency is determined, select the platform (CCB) frequency from the limited options listed in Table 80 and Table 81;
- Check the CCB to SYSCLK ratio to verify a valid ratio can be choose from Table 79;
- If the desired DDR data rate can be same as the CCB frequency, use the synchronous DDR mode; Otherwise, if a higher DDR data rate is desired, use asynchronous mode by selecting a valid DDR data rate to DDRCLK ratio from Table 82. Note that in asynchronous mode, the DDR data rate must be greater than the platform (CCB) frequency. In other words, running DDR data rate lower than the platform (CCB) frequency in asynchronous mode is not supported by MPC8572E.
- Verify all clock ratios to ensure that there is no violation to any clock and/or ratio specification.

19.2 CCB/SYSCLK PLL Ratio

The CCB clock is the clock that drives the e500 core complex bus (CCB), and is also called the platform clock. The frequency of the CCB is set using the following reset signals, as shown in Table 79:

- SYSCLK input signal
- Binary value on LA[29:31] at power up

Note that there is no default for this PLL ratio; these signals must be pulled to the desired values. Also note that, in synchronous mode, the DDR data rate is the determining factor in selecting the CCB bus frequency, because the CCB frequency must equal the DDR data rate. In asynchronous mode, the memory bus clock frequency is decoupled from the CCB bus frequency.

Figure 66. JTAG Interface Connection

21.10 Guidelines for High-Speed Interface Termination

21.10.1 SerDes 1 Interface Entirely Unused

If the high-speed SerDes 1 interface is not used at all, the unused pin should be terminated as described in this section.

The following pins must be left unconnected (float):

- SD1_TX[7:0]
- $\overline{\text{SD1\_TX}}$[7:0]
- Reserved pins C24, C25, H26, H27

The following pins must be connected to XGND_SRDS1:

- SD1_RX[7:0]
- $\overline{\text{SD1\_RX}}$[7:0]
- SD1_REF_CLK
- $\overline{\text{SD1\_REF\_CLK}}$

Pins K32 and C29 must be tied to XV_{DD}_SRDS1. Pins K31 and C30 must be tied to XGND_SRDS1 through a 300-Ω resistor.

The POR configuration pin cfg_srds1_en on TSEC2_TXD[5] can be used to power down SerDes 1 block for power saving. Note that both SVDD_SRDS1 and XVDD_SRDS1 must remain powered.

21.10.2 SerDes 1 Interface Partly Unused

If only part of the high speed SerDes 1 interface pins are used, the remaining high-speed serial I/O pins should be terminated as described in this section.

The following pins must be left unconnected (float) if not used:

- SD1_TX[7:0]
- $\overline{\text{SD1\_TX}}$[7:0]
- Reserved pins: C24, C25, H26, H27

The following pins must be connected to XGND_SRDS1 if not used:

- SD1_RX[7:0]
- $\overline{\text{SD1\_RX}}$[7:0]

Pins K32 and C29 must be tied to XV_{DD}_SRDS1. Pins K31 and C30 must be tied to XGND_SRDS1 through a 300-Ω resistor.

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Document Number: MPC8572EEC
Rev. 7
03/2016